

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
11 May 2023 (11.05.2023)



(10) International Publication Number
WO 2023/079030 A2

(51) International Patent Classification:

C23C 16/04 (2006.01) B33Y 10/00 (2015.01)
C23C 16/455 (2006.01) G02B 5/18 (2006.01)
B29C 64/159 (2017.01) G02B 5/32 (2006.01)

(21) International Application Number:

PCT/EP2022/080734

(22) International Filing Date:

03 November 2022 (03.11.2022)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

21206177.4 03 November 2021 (03.11.2021) EP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— without international search report and to be republished upon receipt of that report (Rule 48.2(g))



WO 2023/079030 A2

(54) Title: DIRECT ATOMIC LAYER DEPOSITION AND/OR ETCHING METHOD

(57) Abstract: The disclosure relates an atomic layer deposition and/or etching method comprising drawing, using a first precursor fluid, on a substrate a first line extending longitudinally and having, in lateral direction, a first linewidth, and drawing, using a second precursor fluid, on the substrate a second line extending longitudinally and having, in lateral direction, a second linewidth. The first and second lines partly overlap one another laterally by less than the first linewidth and the second linewidth, and/or the first and second lines are laterally spaced apart from one another by less than the first linewidth and the second linewidth, such that a first protrusion is formed of which a largest width in lateral direction is smaller than the first linewidth and the second linewidth, and/or a first recess is formed of which a largest width, in lateral direction, is smaller than the first linewidth and the second linewidth.